



3" (76.2mm) AlGaIn/GaN HEMT Epi Wafer Specifications

HEMT on SiC (with GaN cap)

Property	Measurement	Value	Unit	Uniformity
<i>*2DEG Mobility</i>	Contactless Hall	>2000	cm ² /V.s	< %3
<i>*Sheet Charge Density</i>	Contactless Hall	>1,0E+13	cm ⁻²	< %3
<i>**Sheet Resistance</i>	Contactless Hall	< 325	Ohms/Sq	< %3
<i>AlGaIn Barrier Al% Composition</i>	PL	25-27	%	< %3
<i>AlGaIn Barrier Thickness</i>	XRD Fit	18-25	nm	NA
<i>GaN Cap Thickness</i>	XRD Fit	2.0-3.0	nm	NA
<i>Total Film Thickness</i>	White Light Reflection	1.5-2.0	μm	< %3
<i>Final Bow</i>	In-situ Laser	<30	μm	NA

- Substrate: 4H-6H Semi Insulating SiC, 76mm dia., 350μm thick.
- Buffer: Iron/Carbon doped
- Edge Exclusion: 3mm
- * Average of 18 point measurement
- ** Average of 55 point measurement